



10G DFB 1310 nm Laser TOSA Package

Description

A 10 Gb/s edge emitting laser diode in a TO-can package. The Multi-quantum well distributed feedback (DFB) laser is directly modulated (DML) with a RF signal. This device comes with a built in Photodiode monitor to allow Auto-bias operation. Various build configurations allow the user to customize the optical connector as well as the mounting brackets for the device. Optics sub-assembly includes isolator.

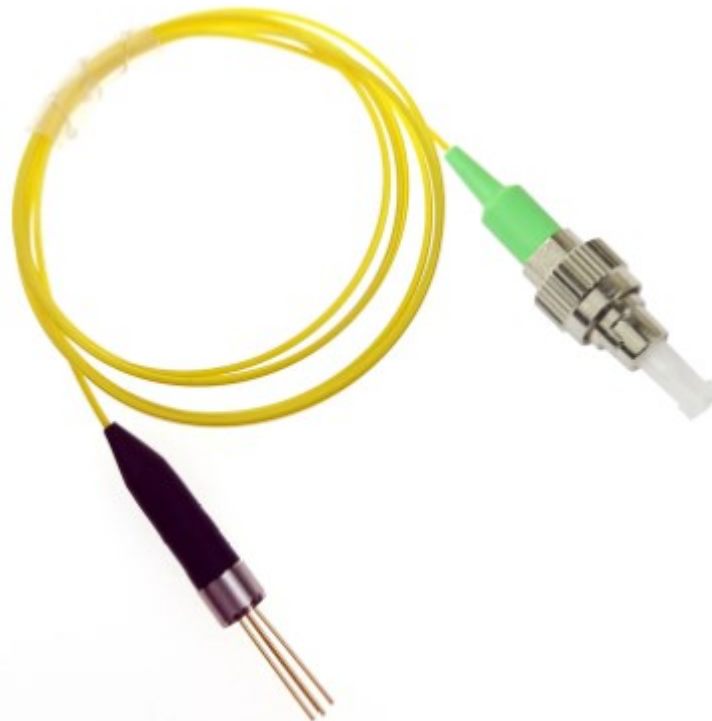
Features

- TO-Can Package
- Single mode Pigtail cable
- 1310 nm CW
- High SFDR
- Built-in InGaAs monitor Photodiode
- Wide temperature operating range
- Built-in Optical Isolator



Applications

- Test and Measurement
- Datacenters
- RF over Fiber (RFoF)



Laser Electro-Optical Characteristics ($T_{op} 23 \pm 3^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Peak Wavelength	λ	1304.5	1310	1317.5	nm	
Threshold Current	I_{th}		5	15	mA	$T=25^{\circ}C$
Front Power	P_o	2.0			mW	$I_f = I_{th} + 20\text{ mA}$
Slope Efficiency	η	0.1			W/A	$I_f = I_{th} + 20\text{ mA}$
Series Resistance	R		8		Ohms	$P_o = 8\text{ mW}$
Forward Voltage	V_f		1.1	1.5	V	$I_f = I_{th} + 20\text{ mA}$
Spectral Wavelength Width (RMS)	$\Delta\lambda$		0.5		nm	$P_o = 5\text{ mW}$ at -20 dB
Frequency Bandwidth	BW	8			GHz	Designed RF board.
Side Mode Suppression Ratio	SMSR	30			dB	
Monitor Current	I_m	0.4	0.5	1.0	mA	$I_{op} = 30\text{ mA}$
Optical Return Loss	ORL			-30	dB	CW = 1310 nm
Tracking Error	T_e	-1.5		1.5	dB	$-40 - 80^{\circ}C$
Rise/Fall Time	T_r/T_f		0.2		ns	20-80%, $I_f = I_{th}$
Optical Isolation	ISO	30			dB	
Relative Intensity Noise	RIN			-130	dB/Hz	

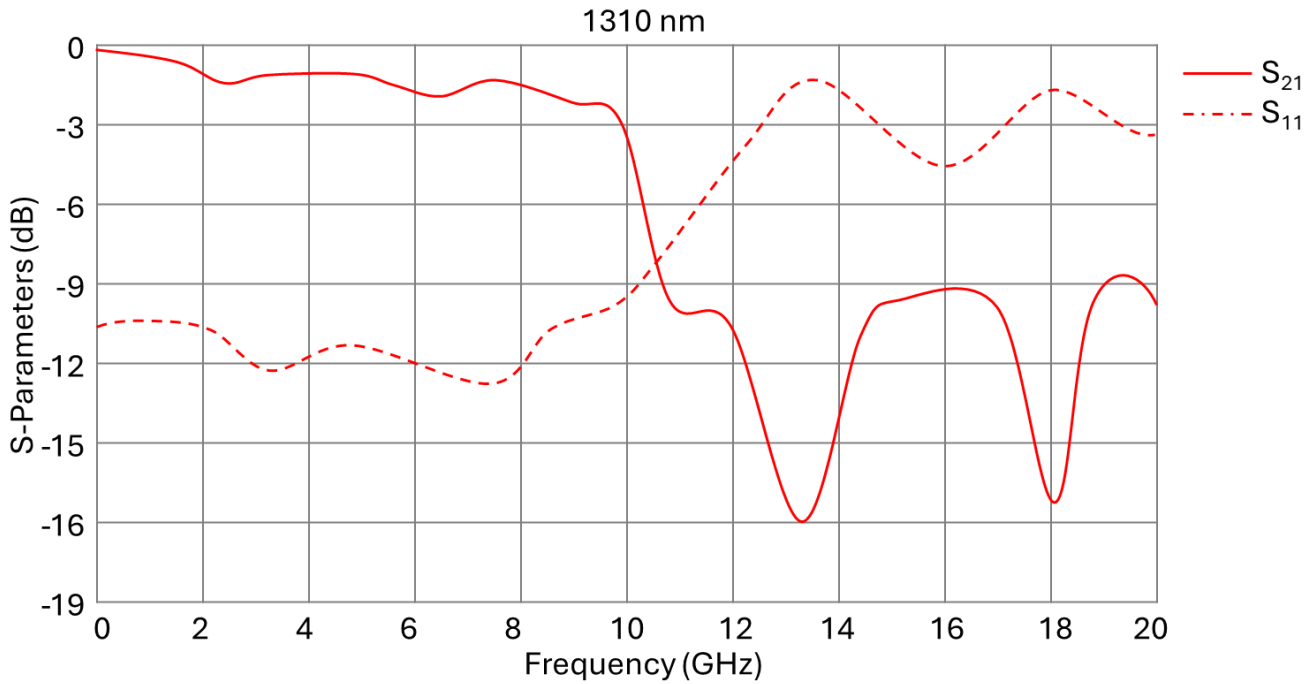
Laser Absolute Maximum Ratings

Parameter	Symbol	Condition	Min.	Max.	Unit
Voltage	V			1.8	V
Forward Current	I_f			80	mA
Storage Temperature	T_{stg}		-25	90	$^{\circ}C$
Storage Humidity	H_{stg}			85	% r.H.
Operating Temperature	T_{op}		-25	85	$^{\circ}C$
Soldering Temperature	T_{st}	60 sec		200	$^{\circ}C$
ESD Susceptibility		HBM	100		V

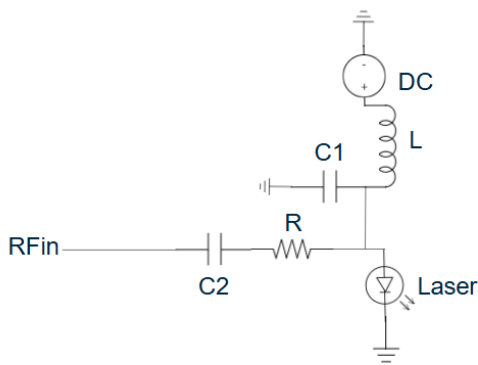
Operating at maximum operating specs for prolong periods of time will damage the device.



Typical Performance Curves (Top = 25°C ± 3°C, 401 Pts, 16 Avgs, 1.5% Smoothing)



Test circuit (Dielectric material - Rogers RO3003® ϵ_r - 3.00 Tan- δ - 0.001)



Test Circuit Configuration

- L – 1.65 μ H Coil inductor (Rated 26 GHz)
- C1 – 470 pF 0201 RF Capacitor
- C2 – 820 pF 0201 RF Capacitor
- R – 5 Ω 0402 RF Resistor

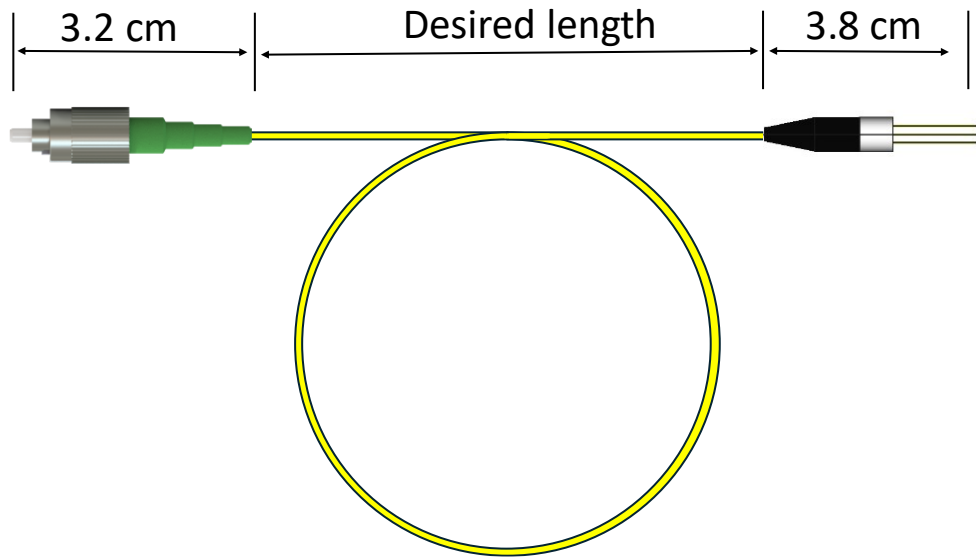
Microstrip traces - 50 Ω ground backed coplanar waveguide (GB-CPW)

Engineering Notes:

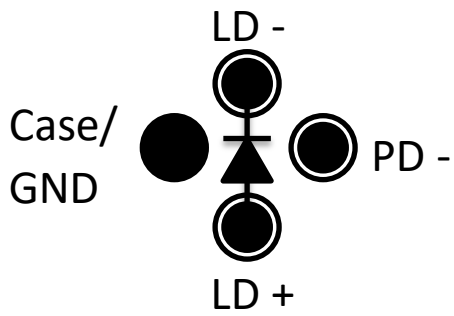
The DFB laser diode is an 8 Ohm series device. Impedance matching the device can be difficult for large bandwidths. To improve S11 impedance matching, a series SMD resistor **R** can be placed which will help lower the S11 < -10 dB. Limiting **R** < 5 dB will help minimize S21 additional losses. If a flatter S21 is more desirable, **C1** can be added to the impedance matching structure. Balancing **R** and **C1** will yield a flatter S21 response with better S11 matching.



Device Dimensions



Device Pin Configuration (Bottom View)



Build A: Standard Configuration

Pin Function:

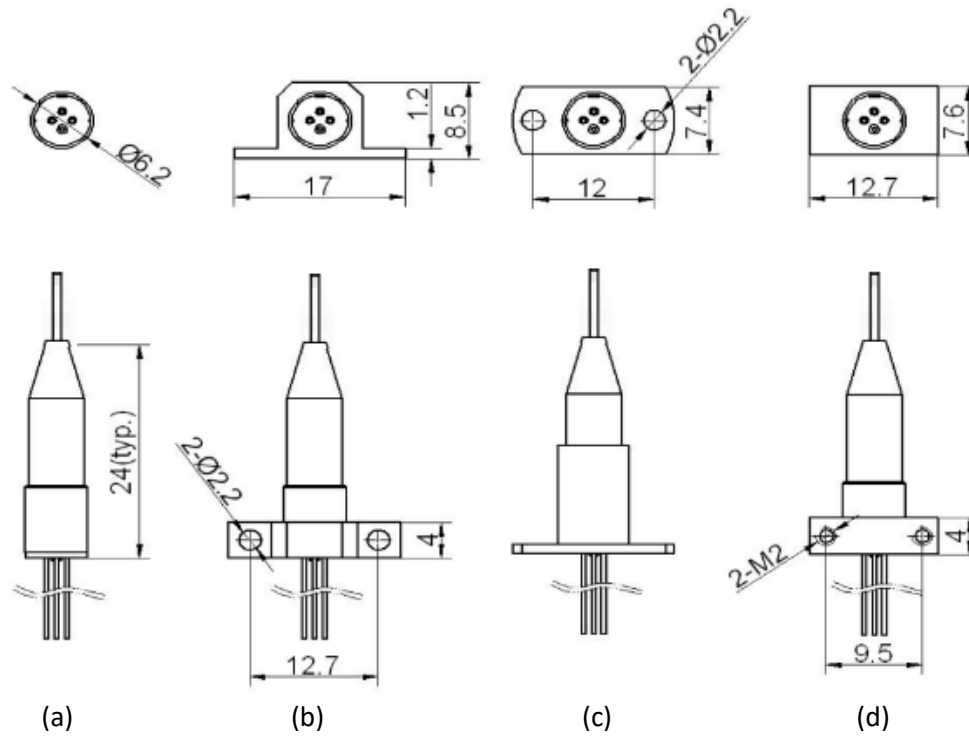
- 1) Laser Anode
- 2) Photodiode Anode Tied to Case Ground
- 3) Laser Cathode
- 4) Monitor PD Cathode

Build B: Custom Pinout

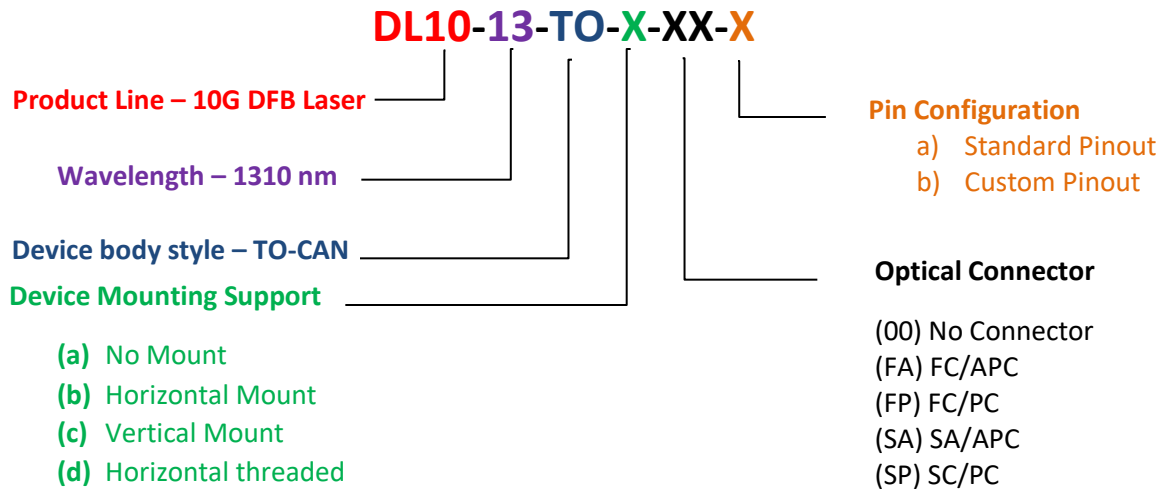
Pinout can be customized



Build Configurations – Mounting Support



Device Nomenclature



Inquiry Information

Sales: For all inquiries regarding sales, please contact Sales@NuPhotonics.com

General: For inquiries regarding custom solutions, general information, or engineering related information please contact Inquiry@NuPhotonics.com



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